

MRF532

CASE 79-02, STYLE 1
TO-39 (TO-205AD)

HIGH FREQUENCY TRANSISTOR

PNP SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Volts
Collector-Base Voltage	V_{CBO}	80	Volts
Emitter-Base Voltage	V_{EBO}	3.5	Volts
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 14.3	Watts $\text{mW}/^\circ\text{C}$
Storage Temperature	T_{stg}	-60 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	70	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10\text{ mA}$)	$V_{(BR)CEO}$	80	—	V_{dc}
Collector-Base Breakdown Voltage ($I_C = 0.1\text{ mA}$)	$V_{(BR)CBO}$	80	—	V_{dc}
Emitter-Base Breakdown Voltage ($I_E = 0.1\text{ mA}$)	$V_{(BR)EBO}$	3.5	—	V_{dc}
Collector Cutoff Current ($V_{CE} = 75\text{ V}$)	I_{CES}	—	10	μA_{dc}
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	h_{FE}	25	—	—
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	—	1.0	V_{dc}
SMALL SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50\text{ mA}$, $V_{CE} = 25\text{ V}$, $f = 100\text{ MHz}$)	f_T	500	—	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	—	4.0	pF

MRF534, MRF536 For Specifications, See MM4049 Data.